

Junhyeok Bang

List of Publications by Citations

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38
papers

878
citations

17
h-index

29
g-index

40
ext. papers

998
ext. citations

6.8
avg, IF

4.12
L-index

#	Paper	IF	Citations
38	Diffusion and thermal stability of hydrogen in ZnO. <i>Applied Physics Letters</i> , 2008 , 92, 132109	3.4	104
37	Deep electron traps and origin of p-type conductivity in the earth-abundant solar-cell material Cu ₂ ZnSnS ₄ . <i>Physical Review B</i> , 2013 , 87,	3.3	97
36	The role of collective motion in the ultrafast charge transfer in van der Waals heterostructures. <i>Nature Communications</i> , 2016 , 7, 11504	17.4	79
35	Atomic and electronic structures of single-layer FeSe on SrTiO ₃ (001): The role of oxygen deficiency. <i>Physical Review B</i> , 2013 , 87,	3.3	76
34	Modification of Defect Structures in Graphene by Electron Irradiation: Ab Initio Molecular Dynamics Simulations. <i>Journal of Physical Chemistry C</i> , 2012 , 116, 16070-16079	3.8	55
33	Electron-rich driven electrochemical solid-state amorphization in Li-Si alloys. <i>Nano Letters</i> , 2013 , 13, 4511-4515	4.5	45
32	Localization and one-parameter scaling in hydrogenated graphene. <i>Physical Review B</i> , 2010 , 81,	3.3	41
31	Multivalency-Induced Band Gap Opening at MoS ₂ Edges. <i>Chemistry of Materials</i> , 2015 , 27, 3326-3331	9.6	39
30	Understanding the presence of vacancy clusters in ZnO from a kinetic perspective. <i>Applied Physics Letters</i> , 2014 , 104, 252101	3.4	33
29	Photoinduced Vacancy Ordering and Phase Transition in MoTe. <i>Nano Letters</i> , 2019 , 19, 3612-3617	11.5	30
28	Regulating energy transfer of excited carriers and the case for excitation-induced hydrogen dissociation on hydrogenated graphene. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2013 , 110, 908-11	11.5	29
27	Molecular doping of ZnO by ammonia: a possible shallow acceptor. <i>Journal of Materials Chemistry C</i> , 2015 , 3, 339-344	7.1	24
26	Triangular Black Phosphorus Atomic Layers by Liquid Exfoliation. <i>Scientific Reports</i> , 2016 , 6, 23736	4.9	24
25	Directional Forces by Momentumless Excitation and Order-to-Order Transition in Peierls-Distorted Solids: The Case of GeTe. <i>Physical Review Letters</i> , 2018 , 120, 185701	7.4	21
24	Carrier-Multiplication-Induced Structural Change during Ultrafast Carrier Relaxation and Nonthermal Phase Transition in Semiconductors. <i>Physical Review Letters</i> , 2016 , 117, 126402	7.4	20
23	Atomic Structure and Diffusion of Hydrogen in ZnO. <i>Journal of the Korean Physical Society</i> , 2009 , 55, 98-102	0.6	18
22	Electronic structure and transport properties of hydrogenated graphene and graphene nanoribbons. <i>New Journal of Physics</i> , 2010 , 12, 125005	2.9	17

21	Difficulty in predicting shallow defects with hybrid functionals: Implication of the long-range exchange interaction. <i>Physical Review B</i> , 2013 , 88,	3.3	15
20	Phase diagram of graphene nanoribbons and band-gap bifurcation of Dirac fermions under quantum confinement. <i>Physical Review B</i> , 2012 , 85,	3.3	15
19	Time-dependent density-functional theory molecular-dynamics study on amorphization of Sc-Sb-Te alloy under optical excitation. <i>Npj Computational Materials</i> , 2020 , 6,	10.9	14
18	Ab initio study of boron segregation and deactivation at Si/SiO ₂ interface. <i>Microelectronic Engineering</i> , 2012 , 89, 120-123	2.5	14
17	Suppression of nonradiative recombination in ionic insulators by defects: Role of fast electron trapping in Tl-doped CsI. <i>Physical Review B</i> , 2013 , 87,	3.3	11
16	Carrier-induced transient defect mechanism for non-radiative recombination in InGaN light-emitting devices. <i>Scientific Reports</i> , 2016 , 6, 24404	4.9	9
15	Carrier Dynamics and Transfer across the CdS/MoS Interface upon Optical Excitation. <i>Journal of Physical Chemistry Letters</i> , 2020 , 11, 6544-6550	6.4	7
14	Phonon-Enabled Carrier Transport of Localized States at Non-Polar Semiconductor Surfaces: A First-Principles-Based Prediction. <i>Journal of Physical Chemistry Letters</i> , 2016 , 7, 3548-53	6.4	5
13	Giant lattice expansion by quantum stress and universal atomic forces in semiconductors under instant ultrafast laser excitation. <i>Physical Chemistry Chemical Physics</i> , 2017 , 19, 24735-24741	3.6	5
12	Phase Transition in a Memristive Suspended MoS Monolayer Probed by Opto- and Electro-Mechanics. <i>ACS Nano</i> , 2020 , 14, 13611-13618	16.7	5
11	Strain-induced indium clustering in non-polar a-plane InGaN quantum wells. <i>Acta Materialia</i> , 2018 , 145, 109-122	8.4	5
10	Optical subpicosecond nonvolatile switching and electron-phonon coupling in ferroelectric materials. <i>Physical Review B</i> , 2020 , 102,	3.3	4
9	Robust ferromagnetism in hydrogenated graphene mediated by spin-polarized pseudospin. <i>Scientific Reports</i> , 2018 , 8, 13940	4.9	4
8	Microscopic Origin for Electrically Benign Small-angle Grain Boundaries in Low-cost Semiconductors. <i>Materials Research Letters</i> , 2014 , 2, 51-56	7.4	3
7	Nonlocal effect of excited carriers on the bond strength of carbazole-based OLED host materials. <i>Physical Review Materials</i> , 2020 , 4,	3.2	3
6	Fully Bottom-Up Waste-Free Growth of Ultrathin Silicon Wafer via Self-Releasing Seed Layer. <i>Advanced Materials</i> , 2021 , 33, e2103708	24	3
5	Doping-induced antiferromagnetic bicollinear insulating state and superconducting temperature of monolayer FeSe systems. <i>Physical Review B</i> , 2018 , 98,	3.3	2
4	Dynamic defect as nonradiative recombination center in semiconductors. <i>Physical Review B</i> , 2019 , 100,	3.3	2

- 3 Substrate effect on hydrogen evolution reaction in two-dimensional MoC monolayers.. *Scientific Reports*, **2022**, 12, 6076 4.9 ○
- 2 Electronic Structure of O-vacancy in High-k Dielectrics and Oxide Semiconductors. *Materials Research Society Symposia Proceedings*, **2011**, 1370, 3
- 1 Fully Bottom-Up Waste-Free Growth of Ultrathin Silicon Wafer via Self-Releasing Seed Layer (Adv. Mater. 41/2021). *Advanced Materials*, **2021**, 33, 2170326 24